

ADD-A-PAK Generation VII Power Modules Thyristor/Thyristor, 95 A



ADD-A-PAK

PRODUCT SUMMARY						
I _{T(AV)}	95 A					
Type	Modules - Thyristor, Standard					

MECHANICAL DESCRIPTION

The ADD-A-PAK generation VII, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- High voltage
- Industrial standard package



- · Low thermal resistance
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- High surge capability
- · Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS VALUES		UNITS			
I _{T(AV)}	85 °C	95				
I _{T(RMS)}		150	۸			
I _{TSM}	50 Hz	2000	A			
	60 Hz	2094				
l ² t	50 Hz	20	kA ² s			
1-1	60 Hz	18.26	KA-S			
I ² √t		200	kA²√s			
V _{RRM}	Range	400 to 1600	V			
T _{Stg}		-40 to 125	°C			
T _J		-40 to 125				



ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 125 °C mA			
	04	400	500	400				
VSK.91	08	800	900	800	15			
V3K.91	12	1200	1300	1200	15			
	16	1600	1700	1600				

ON-STATE CONDUCTION PARAMETER	SYMBOL		TEST COND	ITIONS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	180° conduction	180° conduction, half sine wave, T _C = 85 °C		95	A
Maximum continuous RMS on-state current		DC			150	
Maximum continuous RMS on-state current	I _{T(RMS)}	T _C			78	°C
		t = 10 ms	No voltage		2000	
Maximum peak, one-cycle non-repetitive		t = 8.3 ms	reapplied	Sinusoidal	2094	•
on-state current	I _{TSM}	t = 10 ms	100 % V _{RRM}	half wave, initial $T_{.1} = T_{.1}$ maximum	1682	Α
		t = 8.3 ms	reapplied		1760	
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage		20	kA ² s
		t = 8.3 ms	reapplied	Initial $T_J = T_J$ maximum	18.26	
		t = 10 ms	100 % V _{RRM}		14.14	
		t = 8.3 ms	reapplied		12.91	
Maximum I ² √t for fusing	I ² √t (1)		t = 0.1 ms to 10 ms, no voltage reapplied T _J = T _J maximum			
	(0)	Low level (3)	T _J = T _J maximum		0.97	V
Maximum value of threshold voltage	V _{T(TO)} (2)	High level (4)			1.1	
Maximum value of on-state	(2)	Low level (3)	T _J = T _J maximum		2.76	mΩ
slope resistance	r _t ⁽²⁾	High level (4)			2.38	
Maximum on-state voltage drop	V_{TM}	$I_{TM} = \pi \times I_{T(AV)}$	$I_{TM} = \pi \times I_{T(AV)}$ $T_J = 25 ^{\circ}\text{C}$		1.73	V
Maximum non-repetitive rate of rise of turned on current	dl/dt	$T_J = 25 ^{\circ}\text{C}$, from 0.67 V_{DRM} , $I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500 \text{mA}$, $t_r < 0.5 \mu\text{s}$, $t_p > 6 \mu\text{s}$			150	A/µs
Maximum holding current	I _H	T _J = 25 °C, anode supply = 6 V, resistive load, gate open circuit			250	mA
Maximum latching current	ΙL	T _J = 25 °C, and	ode supply = 6 \	/, resistive load	400	

Notes

⁽¹⁾ I^2t for time $t_x = I^2\sqrt{t} \ x \ \sqrt{t_x}$

⁽²⁾ Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$

^{(3) 16.7 %} $\times \pi \times I_{AV} < I < \pi \times I_{AV}$

 $^{^{(4)}~}I>\pi~x~I_{AV}$



TRIGGERING						
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS	
Maximum peak gate power	P_{GM}			12	W	
Maximum average gate power	P _{G(AV)}			3.0	VV	
Maximum peak gate current	I _{GM}			3.0	Α	
Maximum peak negative gate voltage	- V _{GM}					
		T _J = - 40 °C	Anode supply = 6 V resistive load	4.0	V	
Maximum gate voltage required to trigger	V _{GT}	T _J = 25 °C		2.5		
		T _J = 125 °C		1.7		
		T _J = - 40 °C		270		
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	150	mA	
		T _J = 125 °C		80		
Maximum gate voltage that will not trigger	V_{GD}	T _J = 125 °C, rated V _{DRM} applied		0.25	V	
Maximum gate current that will not trigger	I _{GD}	T _J = 125 °C, rated V _{DRM} applied		6	mA	

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM,} I _{DRM}	T _J = 125 °C, gate open circuit	15	mA				
Maximum RMS insulation voltage	V _{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V				
Maximum critical rate of rise of off-state voltage	dV/dt	T_J = 125 °C, linear to 0.67 V_{DRM}	1000	V/µs				

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	SYMBOL TEST CONDITIONS		UNITS	
Junction operating and storage temperature range		T _J , T _{Stg}		-40 to 125	°C	
Maximum internal thermal resistance, junction to case per leg		R _{thJC}	DC operation 0.22		20044	
Typical thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface flat, smooth and greased	0.1	°C/W	
Mounting targue + 10.0/	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period of	4	Nm	
Mounting torque ± 10 % busbar			3 hours to allow for the spread of the compound.	3	INIII	
Approximate weight				75	g	
Approximate weight				2.7	OZ.	
Case style		JEDEC®	AAP GEN VII	(TO-240AA)		

△R CONDUCTION PER JUNCTION											
DEVICES	8	SINE HALF WAVE CONDUCTION					CTANGUL	AR WAVE C	CONDUCTION	NC	UNITS
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.91	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



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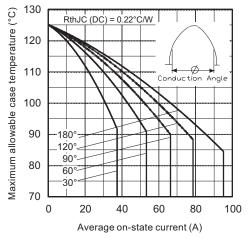


Fig. 1 - Current Ratings Characteristics

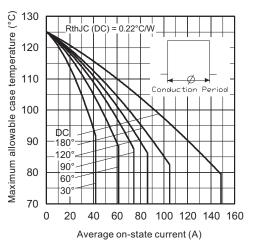


Fig. 2 - Current Ratings Characteristics

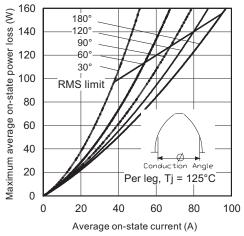


Fig. 3 - On-State Power Loss Characteristics

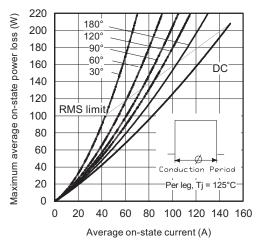
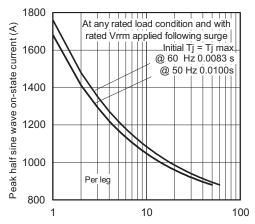


Fig. 4 - On-State Power Loss Characteristics



Number of equal amplitude half cycle current pulses (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

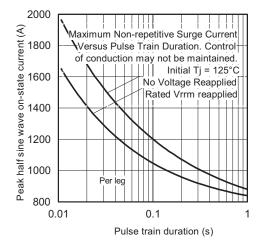


Fig. 6 - Maximum Non-Repetitive Surge Current

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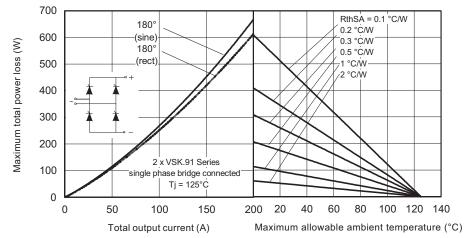


Fig. 7 - On-State Power Loss Characteristics

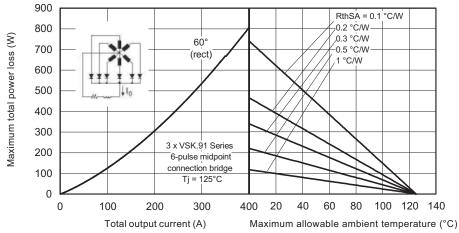


Fig. 8 - On-State Power Loss Characteristics

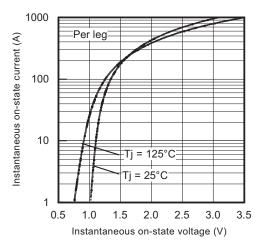


Fig. 9 - On-State Voltage Characteristics

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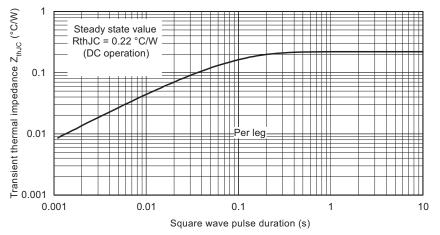


Fig. 10 - Thermal Impedance Z_{thJC} Characteristics

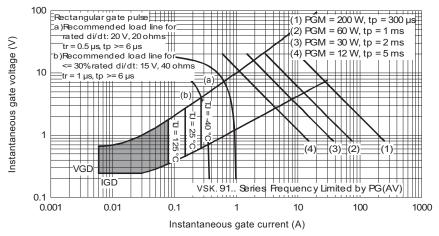
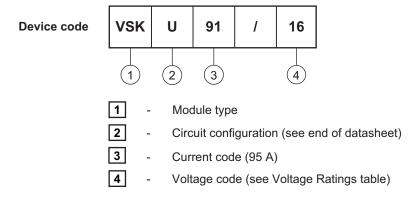


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE



Note

• To order the optional hardware go to www.vishay.com/doc?95172



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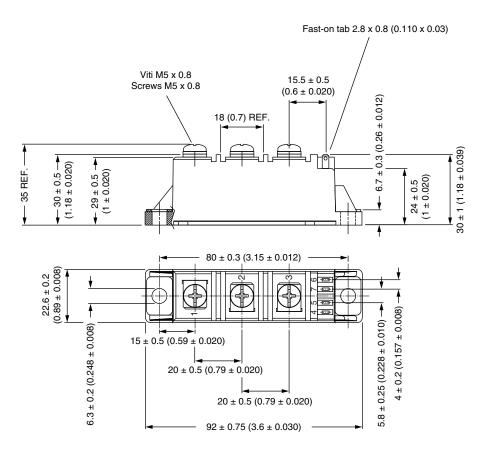
CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs common cathodes	U	VSKU (1) 1 2 (2) (3) (3) (4) (5) (7) (6)
Two SCRs common anodes	V	VSKV (1) 1 2 4 5 7 6 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95368			



ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)





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Revision: 02-Oct-12 Document Number: 91000

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